

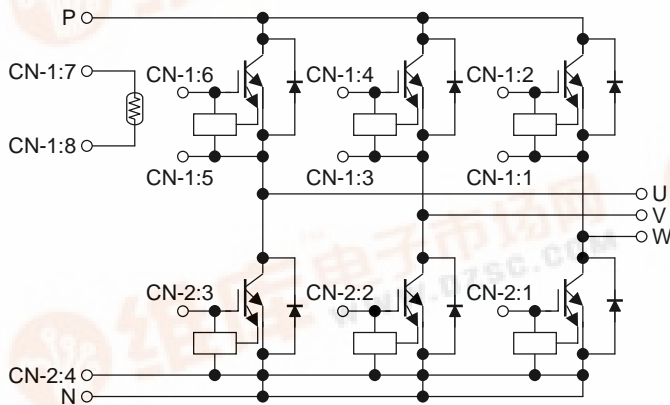
TOSHIBA GTR Module Silicon N Channel IGBT

MG200J6ES60(600V/200A 6in1)

High Power Switching Applications
Motor Control Applications

- Integrates inverter power circuit in to a single package.
- The electrodes are isolated from case.
- Low thermal resistance
- $V_{CE(sat)} = 1.6\text{ V (typ.)}$

Equivalent Circuit

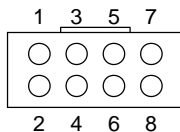
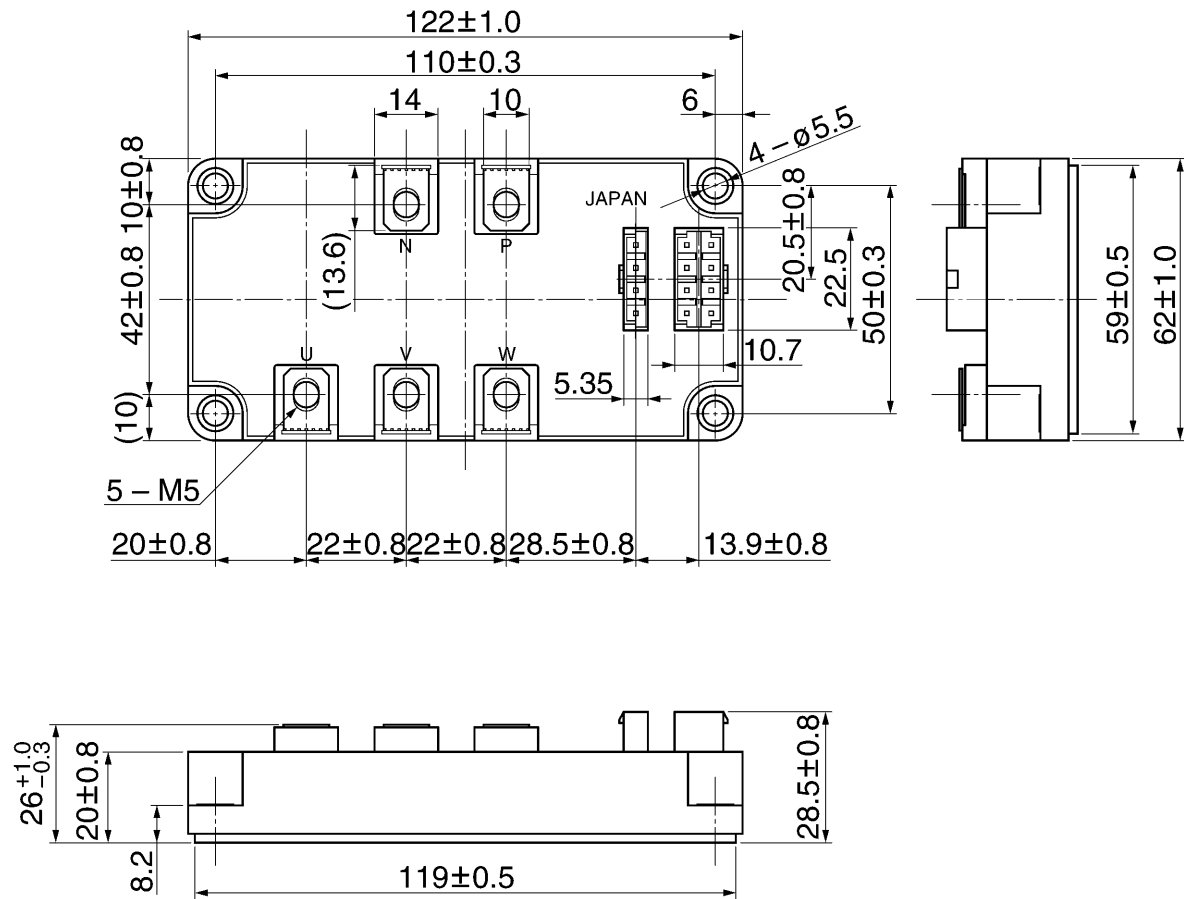


Signal Terminal

| | | | |
|----------|----------|----------|----------|
| CN-1 | | | |
| 1. E (W) | 2. G (W) | 3. E (V) | 4. G (V) |
| 5. E (U) | 6. G (U) | 7. TH1 | 8. TH2 |
| CN-2 | | | |
| 1. G (Z) | 2. G (Y) | 3. G (X) | 4. E (L) |

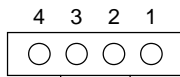
Package Dimensions: 2-123B1A

Unit: mm



CN-1

- | | | | |
|----------|----------|----------|----------|
| 1. E (W) | 2. G (W) | 3. E (V) | 4. G (V) |
| 5. E (U) | 6. G (U) | 7. TH1 | 8. TH2 |



CN-2

- | | | | |
|----------|----------|----------|----------|
| 1. G (Z) | 2. G (Y) | 3. G (X) | 4. E (L) |
|----------|----------|----------|----------|

Maximum Ratings (Ta = 25°C)

| Stage | Characteristics | Symbol | Rating | Unit | |
|---|---------------------------|-------------------|-----------------|------|---|
| Inverter | Collector-emitter voltage | V _{CEs} | 600 | V | |
| | Gate-emitter voltage | V _{GES} | ±20 | V | |
| | Collector current | DC | I _C | 200 | A |
| | | 1 ms | I _{CP} | 400 | |
| | Forward current | DC | I _F | 200 | A |
| | | 1 ms | I _{FM} | 400 | |
| Collector power dissipation (T _c = 25°C) | | P _C | 1000 | W | |
| Module | Junction temperature | T _j | 150 | °C | |
| | Storage temperature range | T _{stg} | -40~125 | °C | |
| | Isolation voltage | V _{isol} | 2500 (AC 1 min) | V | |
| | Screw torque | — | 3 (M5) | N·m | |

Electrical Characteristics (T_j = 25°C)

1. Inverter stage

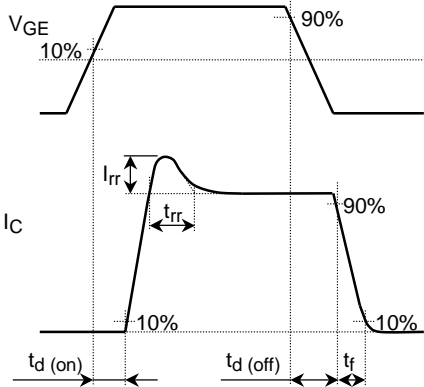
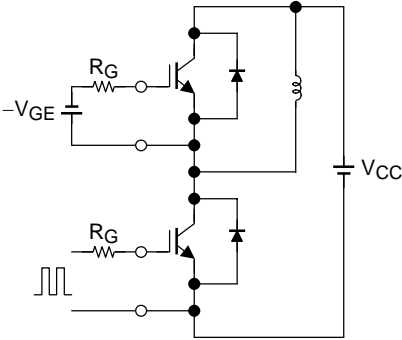
| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit | |
|--------------------------------------|-----------------------|--|---|-------|------|------|----|
| Gate leakage current | I _{GES} | V _{GE} = ±20 V, V _{CE} = 0 | — | — | ±500 | nA | |
| Collector cut-off current | I _{CEs} | V _{CE} = 600 V, V _{GE} = 0 | — | — | 1.0 | mA | |
| Gate-emitter cut-off voltage | V _{GE (off)} | V _{CE} = 5 V, I _C = 200 mA | 5.0 | 6.5 | 8.0 | V | |
| Collector-emitter saturation voltage | V _{CE (sat)} | V _{GE} = 15 V, I _C = 200 A | T _j = 25°C | — | 1.6 | 2.2 | V |
| | | | T _j = 125°C | — | — | 2.2 | |
| Input capacitance | C _{ies} | V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz | — | 33000 | — | pF | |
| Switching time | Turn-on delay time | t _{d (on)} | V _{CC} = 300 V, I _C = 200 A V _{GE} = ±15 V, R _G = 10 Ω (Note 1) | — | — | 1.00 | μs |
| | Turn-off time | t _{off} | | — | — | 1.20 | |
| | Fall time | t _f | | — | — | 0.50 | |
| Reverse recovery time | t _{rr} | — | | — | 0.30 | | |
| Forward voltage | V _F | I _F = 200 A | — | 1.7 | 2.3 | V | |

Note 1: Switching time test circuit & timing chart

2. Module (T_c = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------------------------|-----------------------|---|-----|------|-------|------|
| Zero-power resistance | R ₂₅ | ITM = 0.2 mA | — | 100 | — | kΩ |
| B value | B _{25/85} | T _c = 25°C/T _c = 85°C | — | 4390 | — | K |
| Junction to case thermal resistance | R _{th (j-c)} | Inverter IGBT stage | — | — | 0.125 | °C/W |
| | | Inverter FRD stage | — | — | 0.195 | |
| Case to fin thermal resistance | R _{th (c-f)} | — | — | 0.05 | — | °C/W |

Switching Time Test Circuit & Timing Chart



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